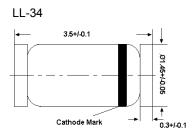
## Silicon Epitaxial Planar Switching Diode

Fast switching diode in MiniMELF case especially suited for automatic surface mounting



Glass case MiniMELF Dimensions in mm

## Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Peak Reverse Voltage		$V_{RM}$	100	V
Reverse Voltage		$V_R$	75	V
Average Rectified Forward Current		I <sub>F(AV)</sub>	200	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 ms at t = 1 µs	I <sub>FSM</sub>	0.5 1 4	А
Power Dissipation		$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature		T <sub>j</sub>	175	$^{\circ}$
Storage Temperature Range		$T_{stg}$	- 65 to + 175	$^{\circ}$

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.











## Characteristics at T<sub>a</sub> = 25℃

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA Pulses	$V_{(BR)R}$	100	-	V
Forward Voltage at I <sub>F</sub> = 10 mA	V <sub>F</sub>	-	1	V
Leakage Current at $V_R$ = 20 V at $V_R$ = 75 V at $V_R$ = 20 V, $T_i$ = 150°C	I <sub>R</sub> I <sub>R</sub>	- - -	25 5 50	nA μA μA
Capacitance at $V_R = 0$ , $f = 1$ MHz	C <sub>tot</sub>	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses tp = 0.1 s, Rise Time < 30 ns, fp = 5 to 100 KHz	V <sub>fr</sub>	-	2.5	V
Reverse Recovery Time at $I_F$ = 10 mA to $I_R$ = 1 mA, Irr = 0.1 x $I_R$ , $V_R$ = 6 V, $R_L$ = 100 $\Omega$	t <sub>rr</sub>	-	4	ns











